

850V Depletion-Mode Power MOSFET

General Features

- ➤ Depletion Mode (Normally On)
- **ESD** Improved Capability
- > Fast Switching Speed
- ➤ RoHS Compliant
- ➤ Halogen-free Available

| BV_{DSX} | R _{DS(ON)(TYP.)} | I _{DSS} |
|------------|---------------------------|------------------|
| 850V | 50 Ω | 80mA |

SOT-223





Applications

- Normally-On Switches
- ➤ Start-up Circuits
- Protection Circuits
- ➤ Solid State Relays
- Power Supply
- > Active Loads

Ordering Information

| Part Number Package | | Marking | Remark | |
|---------------------|---------|---------|--------------|--|
| DMS8550E | SOT-223 | 8550 | Halogen Free | |

Absolute Maximum Ratings

T_A=25°C unless otherwise specified

| Symbol | Parameter | DMS8550E | Unit |
|---------------------|--|------------|------------|
| V_{DSX} | Drain-to-Source Voltage [1] | 850 | V |
| I_D | Continuous Drain Current | 80 | A |
| I_{DM} | Pulsed Drain Current [2] | 320 | mA |
| P_D | Power Dissipation | 1.5 | W |
| V_{GS} | Gate-to-Source Voltage | ±20 | V |
| $T_{ m L}$ | Soldering Temperature Distance of 1.6mm from case for 10 seconds | 300 | $^{\circ}$ |
| T_J and T_{STG} | Operating and Storage Temperature Range | -55 to 150 | |

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

| Symbol | Parameter | DMS8550E | Unit |
|----------------|--------------------------------------|----------|------|
| $R_{	heta JC}$ | Thermal Resistance, Junction-to-Case | 83 | K/W |



Electrical Characteristics

OFF Characteristics

T_A =25°C unless otherwise specified

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Test Conditions |
|---------------------|-----------------------------------|------|------|------|------|------------------------------------|
| BV_{DSX} | Drain-to-Source Breakdown Voltage | 850 | | | V | V_{GS} =-10V, I_D =250 μ A |
| I _{D(OFF)} | Drain-to-Source Leakage Current | | | 10 | μΑ | V_{DS} =850V, V_{GS} =-10V |
| I_{GSS} | Gate-to-Source Leakage Current | | | ±20 | uA | V_{GS} =±20V, V_{DS} =0V |

ON Characteristics

T_A =25°C unless otherwise specified

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Test Conditions |
|----------------------|--------------------------------------|------|------|------|------|--|
| I_{DSS} | Saturated Drain-to-Source Current | 80 | - | | mA | $V_{GS}=0V, V_{DS}=25V$ |
| R _{DS(ON)} | Static Drain-to-Source On-Resistance | | 50 | 80 | Ω | $V_{GS}=0V, I_D=50mA^{[3]}$ |
| V _{GS(OFF)} | Gate-to-Source Cut-off Voltage | -1.5 | | -3.3 | V | V_{DS} =9V, I_{D} =8 μ A |
| gfs | Forward Transconductance | | | | S | V _{DS} =20V, I _D =50mA |

Dynamic Characteristics

Essentially independent of operating temperature

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Test Conditions |
|-------------------|-------------------------------|---------|------|---------|------|--|
| - | | 1,1111. | Typ. | TVILLA. | Cint | Test Conditions |
| C _{iss} | Input Capacitance | | | | | $V_{GS}=-10V$ |
| C_{oss} | Output Capacitance | | | | pF | V _{DS} =50V f=1.0MHz |
| C_{rss} | Reverse Transfer Capacitance | | | | | |
| Q_{g} | Total Gate Charge | | 1 | | | |
| Q_{gs} | Gate-to-Source Charge | | | | пC | V_{GS} =-10V~5V V_{DS} =150V, I_{D} =50mA |
| Q_{gd} | Gate-to-Drain (Miller) Charge | | | | | |

Resistive Switching Characteristics

Essentially independent of operating temperature

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Test Conditions |
|---------------------|---------------------|------|------|------|------|--|
| t _{d(on)} | Turn-on Delay Time | | | | ns | V_{GS} =-10V \sim 0V V_{DD} =50V, I_{D} =50mA R_{G} =10 Ω |
| t _{rise} | Rise Time | | | | | |
| t _{d(off)} | Turn-off Delay Time | | | | | |
| t _{fall} | Fall Time | | | | | |



DMS8550E Provisional Datasheet

| Source-Drain Diode Characteristics | | | | | $T_A = 1$ | 25°C unless otherwise specified | |
|------------------------------------|-------------------|-----------------------|-----|------|-----------|---------------------------------|--|
| | Symbol | Parameter | Min | Тур. | Max. | Units | Test Conditions |
| | V_{SD} | Diode Forward Voltage | | | 1.2 | V | I _{SD} =50mA, V _{GS} =-10V |

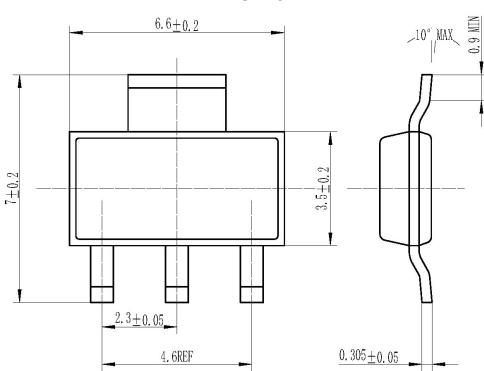
NOTE:

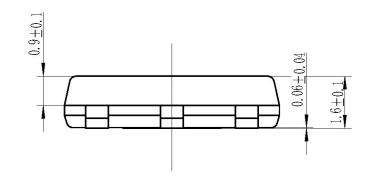
- [1] $T_J = +25^{\circ}C$ to $+150^{\circ}C$
- [2] Repetitive rating, pulse width limited by maximum junction temperature.
- [3] Pulse width \(380 \mu s; \) duty cycle \(\le 2 \%.



Package Dimensions









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